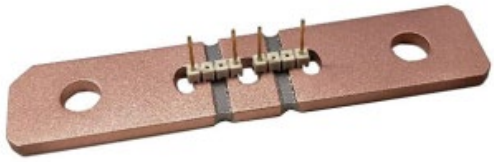
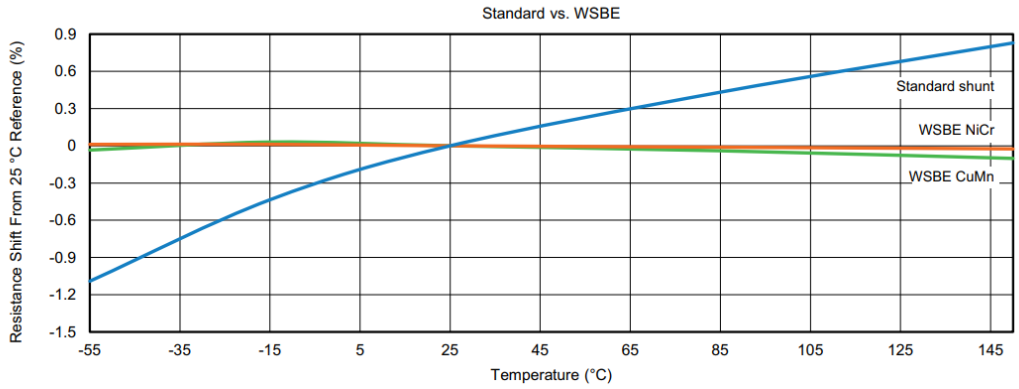
New WSBR Dual-Element Shunt With TCR Immunity for ASIL-D Safety Standards

Our new dual-element WSBR battery shunt features new patent-pending technology that provides high reliability, redundant sensing in a single device with superior temperature stability (without compensation). The device offers many advantageous attributes that help simplify electronic and software complexity, reducing costs while achieving the highest levels of performance and safety.



- High power capability of 40 W
- Proprietary processing technique produces extremely low resistance values from 15 µΩ to 100 µΩ
- Dual element eliminates need for multiple shunts
- Extremely robust welded terminal to element construction
- Solid metal nickel-chrome alloy resistive element with patent pending design for low TCR (< 5 ppm/°C)
- Very low inductance (< 5 nH)
- Low thermal EMF (as low as < 0.8 µV/°C)
- AEC-Q200 qualified

TCR COMPARISON



Useful Links

- WSBR product page

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